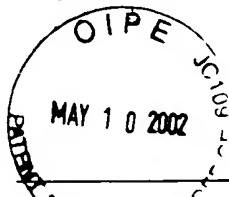




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EXAMINER INITIAL	DOC. NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>RG</i>	5,260,593	11/09/1993	Lee			
	5,305,262	04/19/1994	Yoneda			
	5,311,049	05/10/1994	Tsuruta			
	5,324,675	06/28/1994	Hayabuchi			
	5,338,954	08/16/1994	Shimoji			
	5,349,221	09/20/1994	Shimoji			
	5,350,710	09/27/1994	Hong et al.			
	5,359,554	10/25/1994	Odake et al.			
	5,393,701	02/28/1995	Ko et al.			
	5,394,355	02/28/1995	Uramoto et al.			
	5,414,693	05/09/1995	Ma et al.			
	5,418,176	05/23/1995	Yang et al.			
	5,418,743	05/23/1995	Tomioka et al.			
	5,422,844	06/06/1995	Wolstenholme et al.			
	5,424,567	06/13/1995	Chen			
	5,426,605	06/20/1995	Van Berkel et al.			
	5,434,825	07/18/1995	Harari			
	5,436,481	07/25/1995	Egawa et al.			
	5,455,793	10/03/1995	Amin et al.			
	5,467,308	11/14/1995	Chang et al.			
	5,477,499	12/19/1995	Van Buskirk et al.			
	5,496,753	03/05/1996	Sakurai et al.			
	5,518,942	05/21/1996	Shrivastava			
	5,523,251	06/04/1996	Hong			
	5,553,018	09/03/1996	Wang et al.			
	5,592,417	01/07/1997	Mirabel			
	5,599,727	02/04/1997	Hakozaki et al.			

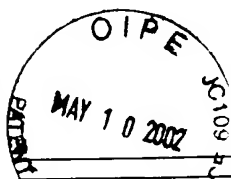
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EXAM. INITIALS	DOC. NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
16/3	5,656,513	08/12/1997	Wang et al.			
	5,712,814	01/27/1998	Fratin et al.			
	5,726,946	03/10/1998	Yamagata et al.			
	5,751,037	05/12/1998	Aozasa et al.			
	5,754,475	05/19/1998	Bill et al.			
	5,760,445	06/02/1998	Diaz			
	5,768,192	06/16/1998	Eitan			
	5,784,314	07/21/1998	Sali et al.			
	5,787,036	07/28/1998	Okazawa			
	5,793,079	08/11/1998	Georgescu et al.			
	5,801,076	09/01/1998	Ghneim et al.			
	5,812,449	09/22/1998	Song			
	5,825,686	10/20/1998	Schmitt-Landsiedel			
	5,836,772	11/17/1998	Chang et al.			
	5,841,700	11/24/1998	Chang			
	5,847,441	12/08/1998	Cutter et al.			
	5,864,164	01/26/1999	Wen			
	5,870,335	02/09/1999	Khan et al.			
	5,903,031	05/11/1999	Yamada et al.			
	5,946,558	08/31/1999	Hsu			
	5,963,412	10/05/1999	En			
	5,973,373	10/26/1999	Krautschneider et al.			
	5,991,202	11/23/1999	Derhacobian et al.			
	6,011,725	01/04/2000	Eitan			
	6,018,186	01/25/2000	Hsu			
	6,020,241	02/01/2000	You et al.			
	6,028,324	02/22/2000	Su et al.			

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EXAMINER INITIAL	DOC. NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>AS</i>	6,034,896	03/07/2000	Ranaweera et al.			
	6,063,666	05/16/2000	Chang et al.			
	6,081,456	06/27/2000	Dadashev			
	6,201,282	03/13/2001	Eitan			
	6,297,096	10/02/2001	Boaz			
	08/902,890	07/30/1997	Eitan			
	08/905,286	07/30/1997	Eitan			
	09/348,720	07/06/1999	Eitan			
	09/413,408	10/06/1999	Eitan			
<i>AS</i>	09/536,125	03/28/2000	Eitan et al.			

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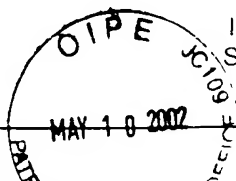
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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
NA	EP 0751560	01/02/1997					
	EP 1073120	01/31/2001					
	GB 1297899	11/29/1972					
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	JP 05021758	01/29/1993					
	JP 07193151	07/28/1995					
NA	JP 09162314	06/20/1997					
	WO 81/00790	03/19/1981					
	WO 96/25741	08/22/1996					

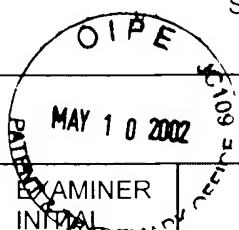
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INFORMATION DISCLOSURE STATEMENT BY APPLICANTS		APPLICANTS Roizin et al.	CONFIRMATION NO. Not Yet Assigned
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